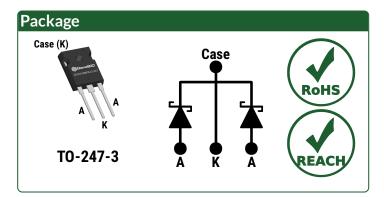
#### Silicon Carbide Schottky Diode



 $V_{RRM}$  = 1200 V  $I_{F(T_C = 153^{\circ}C)}$  = 30 A \*  $Q_C$  = 160 nC \*

#### **Features**

- Low V<sub>F</sub> for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Qc/IF
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V<sub>F</sub>
- High dV/dt Ruggedness



### **Advantages**

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

#### **Applications**

- Power Factor Correction (PFC)
- Electric Vehicles and Battery Chargers
- Solar Inverters
- High Frequency Converters
- Switched Mode Power Supply (SMPS)
- Motor Drives
- Anti-Parallel / Free-Wheeling Diode
- · LED and HID Lighting

Parameter	Symbol	Conditions	Values	Unit	Note
Repetitive Peak Reverse Voltage (Per Leg)	$V_{RRM}$		1200	٧	
Continuous Forward Current (Per Leg / Per Device)	l <sub>F</sub>	$T_C = 100^{\circ}C$ , D = 1	32 / 64		
		$T_C = 135^{\circ}C$ , D = 1	22 / 44	Α	Fig. 4
		$T_C = 153^{\circ}C$ , D = 1	15 / 30		
Non-Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	I <sub>F,</sub> SM	$T_C$ = 25°C, $t_P$ = 10 ms	150	Α	
		$T_C = 150$ °C, $t_P = 10$ ms	120		
Repetitive Peak Forward Surge Current, Half Sine Wave	len.	$T_C$ = 25°C, $t_P$ = 10 ms	90	Α	
(Per Leg)	I <sub>F,RM</sub>	$T_C = 150$ °C, $t_P = 10$ ms	63	A	
Non-Repetitive Peak Forward Surge Current (Per Leg)	I <sub>F,MAX</sub>	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 μs	750	Α	
<sup>2</sup> t Value (Per Leg)	∫i²dt	$T_C$ = 25°C, $t_P$ = 10 ms	112	A <sup>2</sup> s	
Non-Repetitive Avalanche Energy (Per Leg)	E <sub>AS</sub>	L = 2.4 mH, I <sub>AS</sub> = 15 A	270	mJ	
Diode Ruggedness (Per Leg)	dV/dt	V <sub>R</sub> = 0 ~ 960 V	200	V/ns	
Power Dissipation (Per Leg / Per Device)	Ртот	T <sub>C</sub> = 25°C	199 / 398	W	Fig. 3
perating and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>		-55 to 175	°C	

<sup>\*</sup> Per Device





#### **Electrical Characteristics (Per Leg)** Values **Parameter Symbol Conditions** Unit Note Min. Тур. Max. $I_F = 15 A$ , $T_i = 25$ °C 1.5 1.8 ٧ Diode Forward Voltage $V_{\text{F}}$ Fig. 1 $I_F = 15 A$ , $T_i = 175$ °C 1.9 $V_R = 1200 \text{ V, } T_i = 25^{\circ}\text{C}$ 2 10 **Reverse Current** Fig. 2 $I_R$ μΑ $V_R = 1200 \text{ V}, T_j = 175^{\circ}\text{C}$ 17 V<sub>R</sub> = 400 V 55 **Total Capacitive Charge** $Q_{\mathbb{C}}$ nC Fig. 7 $V_R = 800 V$ 80 $I_F \leq I_{F,MAX}$ $dI_F/dt = 200 A/\mu s$ V<sub>R</sub> = 400 V Switching Time < 10 ts ns $V_R = 800 V$ $V_R = 1 V$ , f = 1MHz914 С **Total Capacitance** рF Fig. 6 $V_R$ = 800 V, f = 1MHz 53

Thermal/Package Characteristics										
Parameter	Symbol	Conditions	Values			Heit	Note			
		Conditions	Min.	Тур.	Max.	- Unit	Note			
Thermal Resistance, Junction - Case (Per Leg)	R <sub>thJC</sub>			0.75		°C/W	Fig. 9			
Weight	W <sub>T</sub>			6.1		g				
Mounting Torque	T <sub>M</sub>	Screws to Heatsink			1.1	Nm				





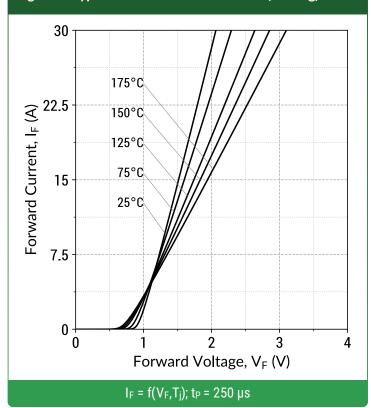


Figure 2: Typical Reverse Characteristics (Per Leg)

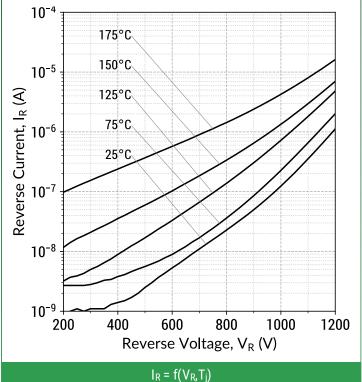


Figure 3: Power Derating Curves (Per Leg)

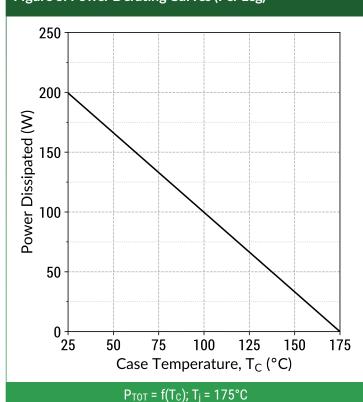


Figure 4: Current Derating Curves (Typical V<sub>F</sub>) (Per Leg)

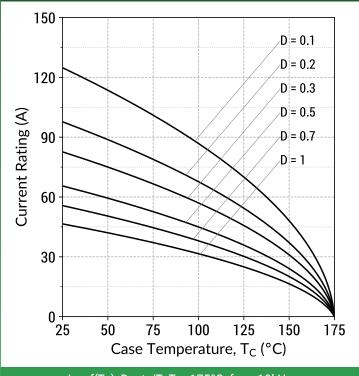
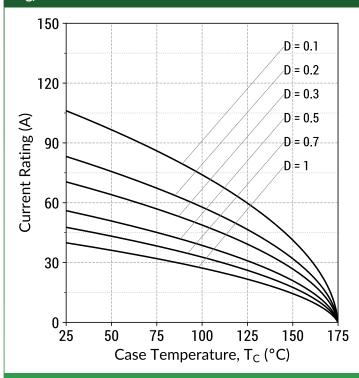


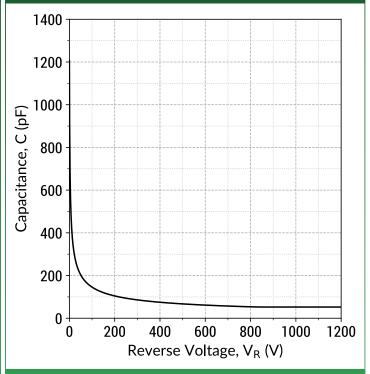


Figure 5: Current Derating Curves (Maximum  $V_F$ ) (Per Leg)



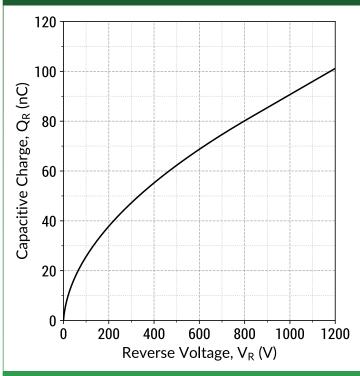
 $I_F = f(T_C); D = t_P/T; T_j \le 175$ °C;  $f_{SW} > 10$ kHz

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics (Per Leg)



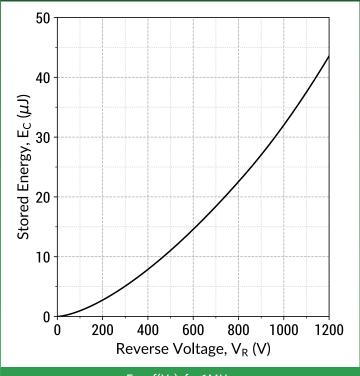
 $C = f(V_R)$ ; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics (Per Leg)



 $Q_C = f(V_R); f = 1MHz$ 

Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics (Per Leg)



 $E_C = f(V_R)$ ; f = 1MHz



Figure 9: Transient Thermal Impedance (Per Leg)

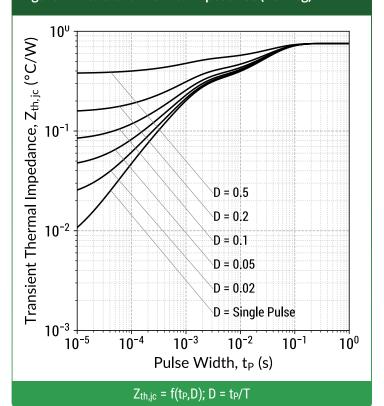
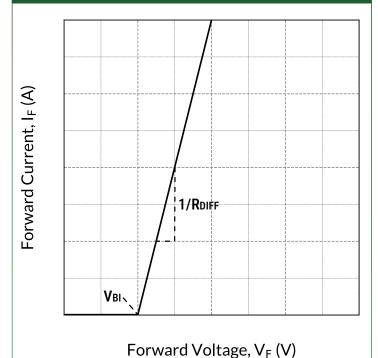


Figure 10: Forward Curve Model (Per Leg)



 $I_F = f(V_F, T_j)$ 

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF}(A)$ 

#### Built-In Voltage (V<sub>BI</sub>):

 $V_{BI}(T_j) = m \times T_j + n (V)$   $m = -0.00123 (V/^{\circ}C)$ n = 0.995 (V)

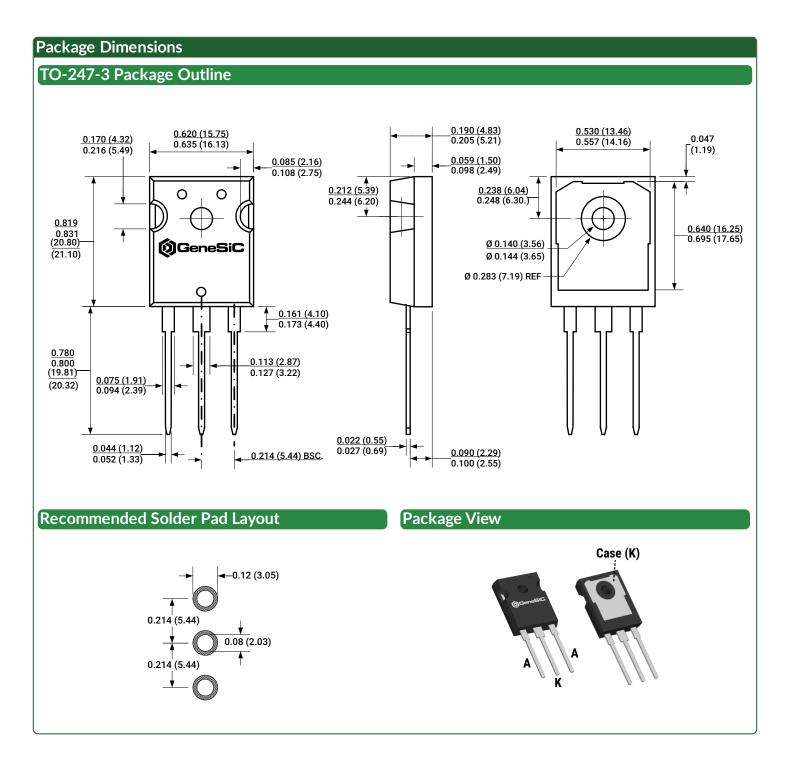
#### Differential Resistance (RDIFF):

 $R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$   $a = 7.95e-07 (\Omega/^{\circ}C^2)$   $b = 0.000113 (\Omega/^{\circ}C)$  $c = 0.0334 (\Omega)$ 

#### **Forward Power Loss Equation:**

 $P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$ 





#### **NOTE**

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





#### **Compliance**

#### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

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#### **Revision History**

Rev 21/Jul: Updated with most recent test data
Supersedes: Rev 19/Apr, Rev 20/Apr, Rev 20/Aug



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